ABSTRACT OF THE DISCLOSURE

Each boosting cell includes: a first n-transistor having a diode connection; a second n-transistor whose gate and drain are connected to a power supply voltage and whose source is connected to the source of the first n-transistor; and a boosting capacitor provided between the drain of the first n-transistor and a boosting clock input terminal to which a clock signal is input. The boosting capacitor is connected to n auxiliary boosting capacitors in parallel via connection switching circuits controlled with boosting ability switching signals as control signals input from the outside.